

Silicon PNP Power Transistors

2SA650

DESCRIPTION

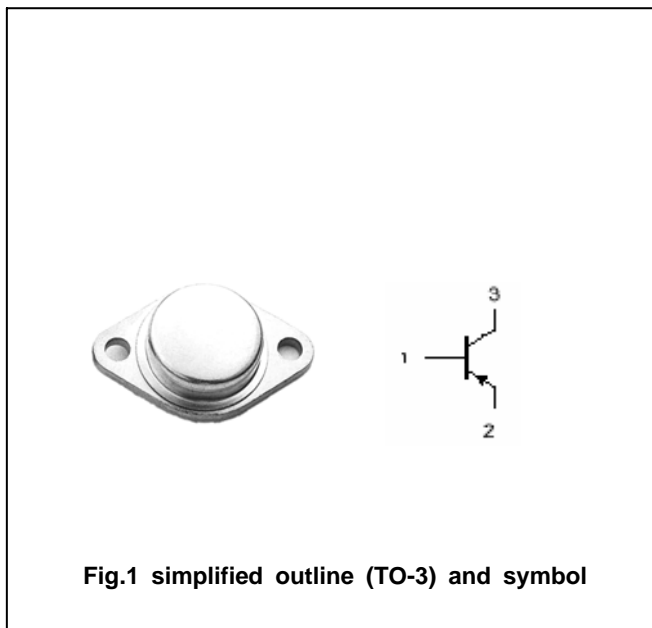
- With TO-3 package
- Wide area of safe operation

APPLICATIONS

- For audio frequency and power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

**Absolute maximum ratings(Ta=℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-150	V
V_{CEO}	Collector-emitter voltage	Open base	-150	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-10	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-25mA ; I _B =0	-150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-5A; I _B =-0.5A			-2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =-150V; I _E =0			-0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-6V; I _C =0			-0.1	mA
h _{FE}	DC current gain	I _C =-2A ; V _{CE} =-5V	30		150	
C _{OB}	Collector output capacitance	I _E =0; V _{CB} =-10V; f=1MHz		500		pF
f _T	Transition frequency	I _C =-1A ; V _{CE} =-5V		10		MHz

PACKAGE OUTLINE

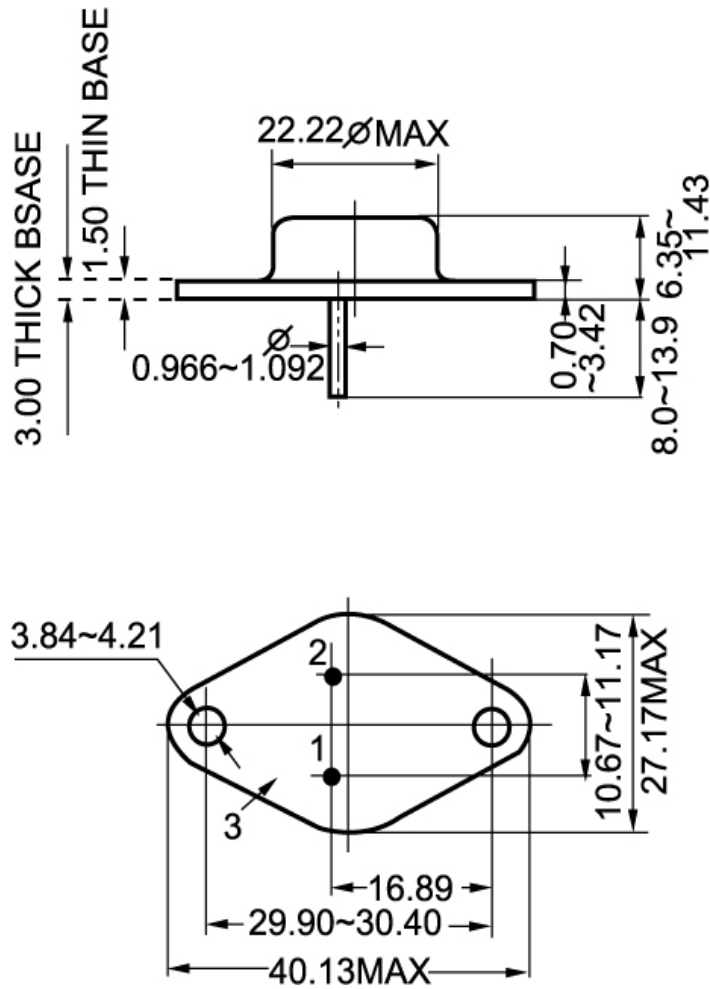


Fig.2 outline dimensions (unindicated tolerance: ± 0.1 mm)